PROCESS CPD94X

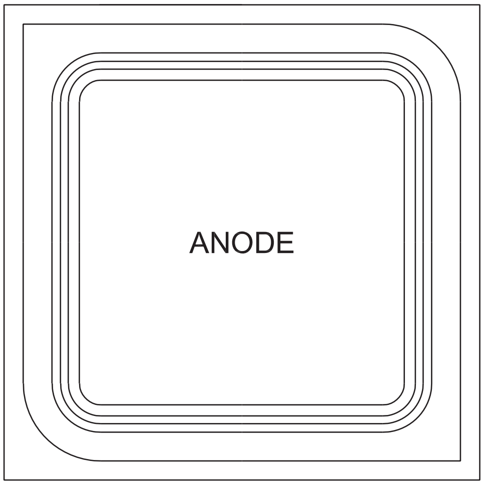
Schottky Diode

0.5 Amp Schottky Diode Chip

PROCESS DETAILS

Die Size	20 x 20 MILS
Die Thickness	5.9 MILS
Anode Bonding Pad Area	16 x 16 MILS
Top Side Metalization	Al - 20,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE CATHODE R0

GROSS DIE PER 5 INCH WAFER
42,213

PRINCIPAL DEVICE TYPES
CMDSH05-4
CMLSH05-4
CMPSH05-4

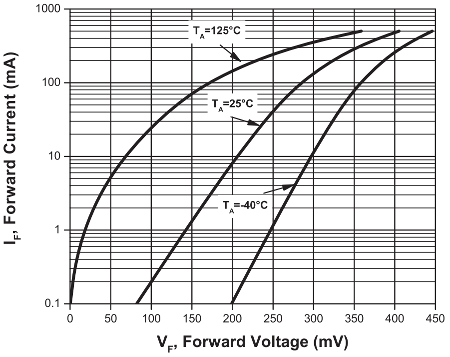
R0 (19-July 2010)

PROCESS CPD94X

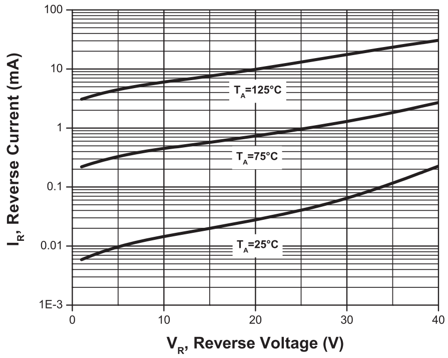
Typical Electrical Characteristics

Central Semiconductor Corp.

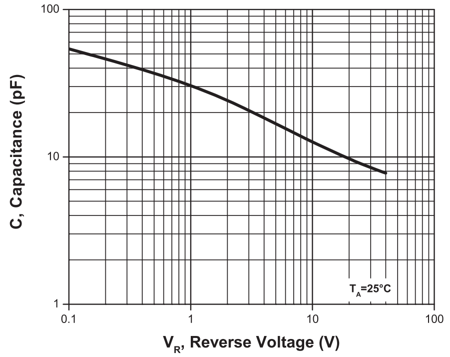
Forward Voltage



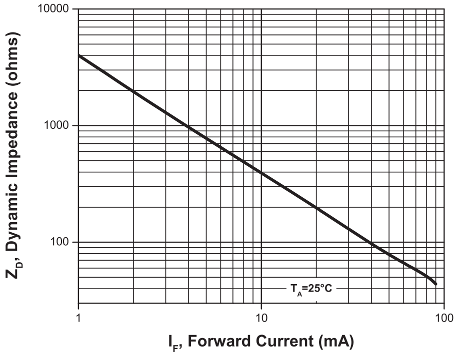
Leakage Current



Capacitance



Forward Dynamic Impedance



Normalized Power Derating